

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-2. (canceled)

3. (currently amended) A ~~material film~~ production method of containing-fullerene or containing-nanotube material film, ~~characterized in that~~ the method comprises:

generating plasma including containment target ions and collision ions having the same polarity as said containment target ions;

irradiating said plasma toward a deposition-assistance substrate[[;]] on which fullerene or nanotube are deposited, by applying a bias voltage of a polarity opposite to that of said containment target ions to said deposition-assistance substrate, to thereby provide said containment target ions and said collision ions with acceleration energies, respectively; and

colliding said collision ions with ~~material molecules~~ constituting a material film fullerene molecules or nanotube molecules, to thereby cause said ~~material molecules~~ fullerene molecules or nanotube molecules to internally contain said containment target ions, respectively.

4. (currently amended) The ~~material film~~ production apparatus method of claim [[1]] 3, ~~characterized in that the method further comprises comprising:~~

depositing said ~~material film~~ fullerene molecules or nanotube molecules on said deposition-assistance substrate, simultaneously with the irradiation of said plasma toward said deposition-assistance substrate.

5. (currently amended) The ~~material film~~ production method of claim [[1]] 3, ~~characterized in that the method further comprises comprising:~~

irradiating said plasma onto said ~~material film~~ fullerene molecules or nanotube molecules previously deposited on said deposition-assistance substrate.

6. (currently amended) A ~~material film~~ production method of containing-fullerene or containing-nanotube material film, ~~characterized in that the method comprises comprising:~~

generating plasma including collision ions;

irradiating said plasma toward a ~~material film~~ fullerene or nanotube previously deposited on ~~said a~~ deposition-assistance substrate;

simultaneously therewith, shooting vapor comprising containment target molecules toward said ~~material film~~ fullerene or nanotube;

colliding said collision ions with ~~material molecules~~ constituting the material film; and

~~simultaneously therewith, causing said material molecules fullerene molecules or nanotube molecules, to thereby cause fullerene molecules or nanotube molecules to internally contain said containment target molecules, respectively.~~

7. (currently amended) The ~~material film~~ production method of claim [[1]] 6, ~~characterized in that the method further comprises comprising:~~

transporting said generated plasma by a magnetic field to thereby irradiate said plasma toward said deposition-assistance substrate.

8. (canceled)

9. (currently amended) The ~~material film~~ production method of claim [[1]] 3, ~~characterized in that wherein~~ said implantation target ions or said containment target ions are alkali metal ions, nitrogen ions, or halogen ions.

10. (currently amended) The ~~material film~~ production method of claim 6, ~~characterized in that wherein~~ said containment target substance is TTF, TDAE, TMTSF, pentacene, tetracene, anthracene, TCNQ, Alq<sub>3</sub>, or F<sub>4</sub>TCNQ.

11. (currently amended) The ~~material film~~ production method of claim 3, ~~characterized in that wherein~~ said collision ions each have a diameter of ~~3.0~~ 3.0 Å or larger.

12. (currently amended) The ~~material film~~ production method of claim 11, ~~characterized in that wherein~~ said collision

ions are fullerene positive ions or fullerene negative ions, respectively.

13. (currently amended) A ~~material film~~ production apparatus of ~~containing-fullerene or containing-nanotube~~ comprising:

a vacuum vessel;

~~magnetic field generation means;~~

plasma generation means for generating plasma including implantation target ions and ~~collision~~ ions having the same polarity as said containment target ions;

~~an electric potential body configured to control a density of said implantation target ions by applying a control voltage to said electric potential body;~~

a deposition-assistance substrate for depositing a ~~material film~~ fullerene or nanotube thereon;

magnetic field generation means for transporting and irradiating said plasma to said deposition-assistance substrate;  
and

a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

14. (currently amended) The ~~material film~~ production apparatus of claim 13, ~~characterized in that~~ wherein said electric potential body comprises electroconductive wires in a lattice pattern.

15. (currently amended) A ~~material film~~ production apparatus of containing-fullerene or containing-nanotube comprising:

a vacuum vessel;  
~~magnetic field generation means;~~  
plasma generation means for generating plasma including containment target ions;  
collision ion generation means for generating collision ions;  
a deposition-assistance substrate for depositing a ~~material film~~ fullerene or nanotube thereon;  
magnetic field generation means for transporting and irradiating said plasma to said deposition-assistance substrate;  
and  
a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

16. (currently amended) A ~~material film~~ production apparatus of containing-fullerene or containing-nanotube comprising:

a vacuum vessel;  
~~magnetic field generation means;~~  
plasma generation means for generating plasma including collision ions;  
a deposition-assistance substrate for depositing a ~~material film~~ fullerene or nanotube thereon;

magnetic field generation means for transporting and  
irradiating said plasma to said deposition-assistance substrate;

containment target molecule shooting means for shooting vapor including containment target molecules to said deposition-assistance substrate; and

a bias power supply configured to apply a bias voltage to said deposition-assistance substrate.

17. (new) The production method of claim 3, further comprising:

measuring an electric current flowing between the deposition-assistance substrate and a bias power supply for applying the bias voltage thereto, to thereby measure the density of the containment target ions.